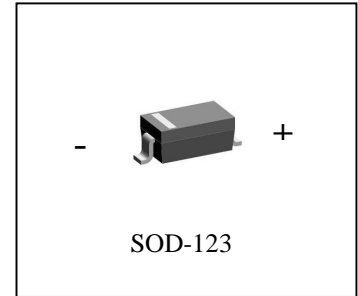


MM1Z2V2B~MM1Z39B

SILICON PLANAR ZENER DIODES

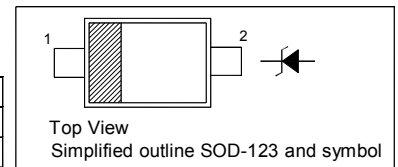
Features

- Total power dissipation: max. 500 mW
- Small plastic package suitable for surface mounted design
- High reliability



PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Power Dissipation	P _{tot}	500	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{Stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R _{thA}	340	°C/W
Forward Voltage at I _F = 10 mA	V _F	0.9	V

MM1Z2V2B~MM1Z39B

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Type	Zener Voltage Range ¹⁾			Dynamic Impedance ²⁾		Reverse Leakage Current	
	V_{znom} V	I_{ZT} mA	for V_{ZT} V	$Z_{ZT}(\text{Max.})$ Ω	at I_{ZT} mA	$I_R(\text{Max.})$ μA	at V_R V
MM1Z2V2B	2.2	5	2.1...2.4	100	5	120	0.7
MM1Z2V4B	2.4	5	2.3...2.65	100	5	120	1
MM1Z2V7B	2.7	5	2.65...2.95	110	5	120	1
MM1Z3V0B	3.0	5	2.95...3.25	120	5	50	1
MM1Z3V3B	3.3	5	3.25...3.55	120	5	20	1
MM1Z3V6B	3.6	5	3.6...3.845	100	5	10	1
MM1Z3V9B	3.9	5	3.89...4.16	100	5	5	1
MM1Z4V3B	4.3	5	4.17...4.43	100	5	5	1
MM1Z4V7B	4.7	5	4.55...4.75	100	5	2	1
MM1Z5V1B	5.1	5	4.98...5.2	80	5	2	1.5
MM1Z5V6B	5.6	5	5.49...5.73	60	5	1	2.5
MM1Z6V2B	6.2	5	6.06...6.33	60	5	1	3
MM1Z6V8B	6.8	5	6.65...6.93	40	5	0.5	3.5
MM1Z7V5B	7.5	5	7.28...7.6	30	5	0.5	4
MM1Z8V2B	8.2	5	8.02...8.36	30	5	0.5	5
MM1Z9V1B	9.1	5	8.85...9.23	30	5	0.5	6
MM1Z10B	10	5	9.77...10.21	30	5	0.1	7
MM1Z11B	11	5	10.76...11.22	30	5	0.1	8
MM1Z12B	12	5	11.74...12.24	30	5	0.1	9
MM1Z13B	13	5	12.91...13.49	37	5	0.1	10
MM1Z15B	15	5	14.34...14.98	42	5	0.1	11
MM1Z16B	16	5	15.85...16.51	50	5	0.1	12
MM1Z18B	18	5	17.56...18.35	65	5	0.1	13
MM1Z20B	20	5	19.52...20.39	85	5	0.1	15
MM1Z22B	22	5	21.54...22.47	100	5	0.1	17
MM1Z24B	24	5	23.72...24.78	120	5	0.1	19
MM1Z27B	27	5	26.19...27.53	150	5	0.1	21
MM1Z30B	30	5	29.19...30.69	200	5	0.1	23
MM1Z33B	33	5	32.15...33.79	250	5	0.1	25
MM1Z36B	36	5	35.07...36.87	300	5	0.1	27
MM1Z39B	39	5	37...41	100	5	2	30

¹⁾ V_Z is tested with pulses(20 ms).

²⁾ Z_{ZT} is measured at I_Z by given a very small A.C. current signal.